AMENDMENTS TO THE CLAIMS:

If entered, this listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

 (currently amended) A circuit to drive a high-voltage H-bridge using CMOS technology comprising:

a control logic circuit having an-inputs and an-output, wherein the a first input is a signal defining the direction of the current between the mid-points of the H-bridge and a second -input comprises control signals defining the behavior of said H-bridge and the output are control signals for the high-side and low-side drivers of said H-bridge;

a power management module having an input and an-outputs wherein the input is a battery voltage and a first the output is a voltage to feed the low-side drivers and a second output feeds a means to drive at the battery voltage level;

said charge pumpmeans to drive at the battery voltage level to drive the high-side drivers of the H-bridge and to drive a means for reverse supply protection, wherein said charge pump comprises a switching network controlled by a clocking scheme;

said means for reverse supply protection;

said two high-side drivers of the H-bridge having an-inputs and an output, wherein the a first input are said output control signals from said control logic circuit and a second input is a voltage from said charge pumpeharge pump and

<u>each</u>the output is driving <u>one of two</u>the high-side transistors of said H-bridge via a resistor <u>each</u>;

a first two-voltage dividers, wherein a first resistor is coupled between the output of the first of said two high-side drivers and a first midpoint of said H-bridge and a second resistor is coupled between said first midpoint and ground voltage, keeping the reference voltage of said first high-side drivers on the voltage levels of thesaid first -midpoints of said H-bridge;

a second voltage divider, wherein a first resistor is coupled between

the output of the second of said two high-side drivers and a second midpoint of said

H-bridge and a second resistor is coupled between said second midpoint and ground

voltage, keeping the reference voltage of said second high-side driver on the voltage

level of said second midpoint of said H-bridge;

<u>said</u> two low-side drivers having <u>an-input</u> and an output, wherein thea <u>first input input</u> are <u>said output</u> control signals from said control logic circuit and a <u>second input is the first output voltage from of</u> said power management module and <u>each</u> the output is driving <u>one of two</u> the <u>correspondent low-side transistors of said H-bridge</u>;

——<u>said</u> two high-side transistors of said H-bridge being connected between the battery voltage and the midpoints of said H-bridge having <u>each itstheir</u> gates connected to the output of one of said two related high-side drivers via one of said resistors each;

said two low-side transistors of said H-bridge being connected between the mid-points of said H-bridge and ground having their gates connected to the output of one of said related lowhigh-side drivers; and

a load between the midpoints of said H-bridge.

2. (currently amended) The circuit of claim 1 wherein said control logic <u>circuit</u>, said power management module, the switching part of said means to increase battery voltage, said two high-side drivers, said voltage dividers, and said low-side drivers are all implemented on one ASIC.

Claims 3-5 (canceled)

(currently amended) The circuit of claim 1 wherein said module for reverse supply
protection and said high-side and low-side transistors are implemented outside of
an ASIC.

Claims 7-8 (canceled)

- (currently amended): The circuit of claim 81 wherein said clocking scheme is a two-phase clocking scheme.
- **10.** (currently amended): The circuit of claim **71** wherein said charge pump comprises two external capacitors.
- **11.** (original): The circuit of claim **10** wherein said two external capacitors are ceramic capacitors.

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- 12. (currently amended): The circuit of claim 1 wherein said <u>module</u>means for <u>external reverse</u> supply protection is driving a transistor to inhibit any reverse supply situation.
- 13.(original): The circuit of claim 12 wherein said transistor is a N-channel MOS power transistor.
- 14. (original)The circuit of claim 1 wherein said two high-side transistors are N-channel MOS power transistors.
- **15.** (original) The circuit of claim **1** wherein said two low-side transistors are N-channel MOS power transistors.
- **16.** (original) The circuit of claim **1** wherein the load of said H-bridge is controlled by signals using pulse width modulation (PWM).
- **17.** (original): The circuit of claim 1 wherein said load between the midpoints of said H-bridge is a DC-motor.
- **18.** (original) The circuit of claim **17** wherein the direction of the rotation of said DC-motor is controlled by a direction bit.
- 19. (original) The circuit of claim 17 wherein the velocity of said DC motor is

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controlled by signals using pulse width modulation (PWM).

Claims 20 - 21 (canceled)

- 22. (original)The circuit of claim 1 wherein said high-side drivers and said low said drivers work in a push-pull configuration.
- 23. (original): The circuit of claim 1 wherein each of said high-drivers comprises:

 a semiconductor switch;

an analog controller having an input and an output, wherein the input are pulses defining the cycles of said semiconductor switch and the output are currents to control said switch; and

a means to provide a bias voltage to said semiconductor switch.

- **24.** (original): The circuit of claim **23** wherein said semiconductor switch is a CMOS FET.
- **25.** (original): The circuit of claim **23** wherein said means to provide a bias voltage is a resistor.

Claims 26-44 (canceled)